

Final datasheet

CoolSiC™ Hybrid Discrete : CoolSiC™ 1200 V SiC MOSFET G2 co-packed with soft, fast recovery Emitter Controlled 7 diode for reverse-polarity protection

Features

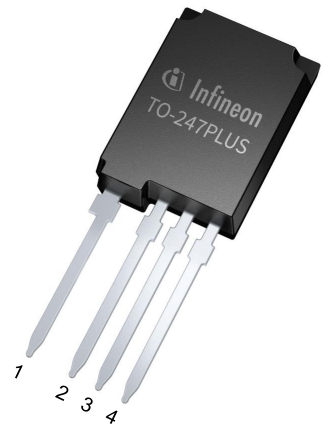
- $V_{DSS} = 1200\text{ V}$ at $T_{vj} = 25^\circ\text{C}$
- $I_{DDC} = 56\text{ A}$ at $T_c = 100^\circ\text{C}$
- $R_{DS(on)} = 18\text{ m}\Omega$ at $V_{GS} = 18\text{ V}$, $T_{vj} = 25^\circ\text{C}$
- Reverse-polarity protection diode with $I_F = 81\text{ A}$ at $T_c = 100^\circ\text{C}$
- Very low switching losses
- Optimized for MPPT boost converter in solar applications
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.2\text{ V}$
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Soft and low Q_{rr} diode with $V_F = 1.6\text{ V}$ at $T_c = 175^\circ\text{C}$
- Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>

Potential applications

- String inverter

Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



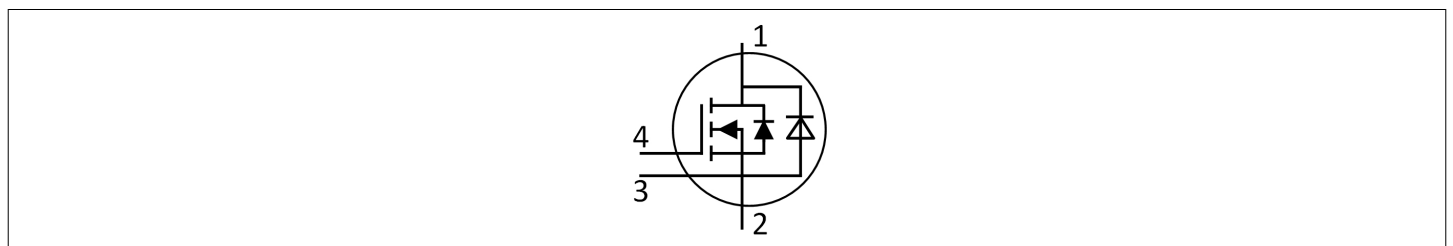
- Halogen-free
- Green
- Lead-free
- RoHS

Description

Pin definition:

- 1 – Drain
- 2 – Source
- 3 – Kelvin sense contact
- 4 – Gate

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction (only for 4pin, TO263-7L)



Type	Package	Marking
IMY120R018CM2H	PG-TO247-4-U10	12M2HC018

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1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	Wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET thermal resistance, junction-case	$R_{th(j-c)}$			0.41	0.53	K/W
Reverse-polarity protection diode thermal resistance, junction-case	$R_{th(j-c)}$			0.31	0.42	K/W
Comparative Tracking Index	CTI	IEC 60112 (material group 1 according to IEC 60664-1)	600			V

2 MOSFET

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25\text{ °C}$	1200	V	
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18\text{ V}$	$T_c = 25\text{ °C}$	80	A
			$T_c = 100\text{ °C}$	56	
Peak drain current, t_p limited by $T_{vj(max)}$ ¹⁾	I_{DM}	$V_{GS} = 18\text{ V}$	280	A	
Gate-source voltage, max. transient voltage ²⁾	V_{GS}	$t_p \leq 0.5\ \mu\text{s}, D < 0.01$	-10...25	V	
Gate-source voltage, max. static voltage	V_{GS}		-7...23	V	
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25\text{ °C}$	280	W
			$T_c = 100\text{ °C}$	141	

1) Verified by design

2) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

Table 3 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 37.4 \text{ A}$	$T_{vj} = 25 \text{ }^\circ\text{C}$, $V_{GS(on)} = 18 \text{ V}$		18	23	mΩ
			$T_{vj} = 150 \text{ }^\circ\text{C}$, $V_{GS(on)} = 18 \text{ V}$		37		
			$T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GS(on)} = 18 \text{ V}$		43		
			$T_{vj} = 25 \text{ }^\circ\text{C}$, $V_{GS(on)} = 15 \text{ V}$		23		
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 11.8 \text{ mA}$, $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20 \text{ V}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$	3.5	4.2	5.1	V
			$T_{vj} = 175 \text{ }^\circ\text{C}$		3.2		
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1200 \text{ V}$, $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$			350	μA
			$T_{vj} = 175 \text{ }^\circ\text{C}$		957		
Gate leakage current	I_{GSS}	$V_{DS} = 0 \text{ V}$	$V_{GS} = 23 \text{ V}$			120	nA
			$V_{GS} = -10 \text{ V}$			-120	
Forward transconductance	g_{fs}	$I_D = 37.4 \text{ A}$, $V_{DS} = 20 \text{ V}$		28.6		S	
Internal gate resistance	$R_{G,int}$	$f = 1 \text{ MHz}$, $V_{AC} = 25 \text{ mV}$		2.2		Ω	
Input capacitance	C_{iss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$		2885		pF	
Output capacitance	C_{oss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$		134		pF	
Reverse transfer capacitance	C_{rss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$		7.9		pF	
C_{oss} stored energy	E_{oss}	Calculated based on $C_{oss} = f(V_{DD})$		54		μJ	
Output charge	Q_{oss}	Calculated based on $C_{oss} = f(V_{DD})$		197		nC	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{DS} = 0 \dots 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, Calculated based on E_{oss}		169		pF	
Effective output capacitance, time related	$C_{o(tr)}$	$I_D = \text{constant}$, $V_{DS} = 0 \dots 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, Calculated based on Q_{oss}		246		pF	
Total gate charge	Q_G	$V_{DD} = 800 \text{ V}$, $I_D = 37.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		73		nC	
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800 \text{ V}$, $I_D = 37.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		16.3		nC	
Gate-drain charge	Q_{GD}	$V_{DD} = 800 \text{ V}$, $I_D = 37.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		16.8		nC	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800 \text{ V}$, $I_D = 37.4 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.8 \text{ } \Omega$, $L_\sigma = 12 \text{ nH}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		14		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$		13.6		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time	t_r	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	14		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	13.6		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	26.8		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	31.6		
Fall time	t_f	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	11.2		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	12.8		
Turn-on energy	E_{on}	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	381		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	392		
Turn-off energy	E_{off}	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	74		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	76		
Total switching energy	E_{tot}	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	455		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	468		
Turn-on energy at -5 V	E_{on}	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = -5/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	346		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	364		
Turn-off energy at -5 V	E_{off}	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = -5/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	55		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	55		
Total switching energy at -5 V	E_{tot}	$V_{DD} = 800\text{ V}, I_D = 37.4\text{ A},$ $V_{GS} = -5/18\text{ V},$ $R_{G,ext} = 2.8\ \Omega, L_\sigma = 12\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	401		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	419		
Virtual junction temperature	T_{vj}		-40		175	$^\circ\text{C}$

Note: Characteristics at $T_{vj} = 25\text{ }^\circ\text{C}$, unless otherwise specified.
Dynamic test circuit see Figure F, 2nd device SiC Schottky diode IDWD40G120C5.

3 Reverse-polarity protection diode

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Diode forward current, limited by T_{vjmax}	I_F	limited by bondwire	$T_c = 25\text{ }^\circ\text{C}$	106	A
			$T_c = 100\text{ }^\circ\text{C}$	81	

(table continues...)

Table 5 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}		225	A
Power dissipation	P_{tot}	$T_c = 25\text{ °C}$	356	W
		$T_c = 100\text{ °C}$	178	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode forward voltage	V_F	$I_F = 75\text{ A}$	$T_{vj} = 25\text{ °C}$	1.65	2.15	V
			$T_{vj} = 175\text{ °C}$	1.6		
Diode reverse recovery charge	Q_{rr}	$I_F = 37.4\text{ A}$, $V_{DD} = 800\text{ V}$, $R_{G,ext} = 2.8\text{ }\Omega$, Opposite MOSFET $V_{GS} = 0/18\text{ V}$, Q_{rr} includes also Q_C	$T_{vj} = 25\text{ °C}$	4.4		μC
			$T_{vj} = 175\text{ °C}$	11.8		
Diode peak reverse recovery current	I_{rrm}	$I_F = 37.4\text{ A}$, $V_{DD} = 800\text{ V}$, $R_{G,ext} = 2.8\text{ }\Omega$, Opposite MOSFET $V_{GS} = 0/18\text{ V}$	$T_{vj} = 25\text{ °C}$	138		A
			$T_{vj} = 175\text{ °C}$	208		
Diode reverse recovery energy	E_{rec}	$I_F = 37.4\text{ A}$, $V_{DD} = 800\text{ V}$, $R_{G,ext} = 2.8\text{ }\Omega$, Opposite MOSFET $V_{GS} = 0/18\text{ V}$, Q_{rr} includes also Q_C	$T_{vj} = 25\text{ °C}$	2.7		mJ
			$T_{vj} = 175\text{ °C}$	7.4		
Virtual junction temperature	T_{vj}		-40		175	$^{\circ}\text{C}$

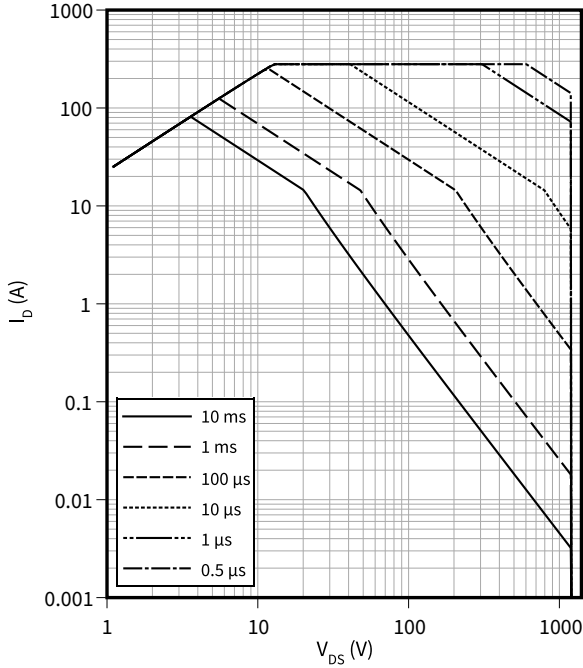
Note: Dynamic test circuit see Figure G, 2nd device: reverse-polarity protection co-packed diode, $V_{GS} = 0\text{ V}$.

4 Characteristics diagrams

Safe operating area (SOA)

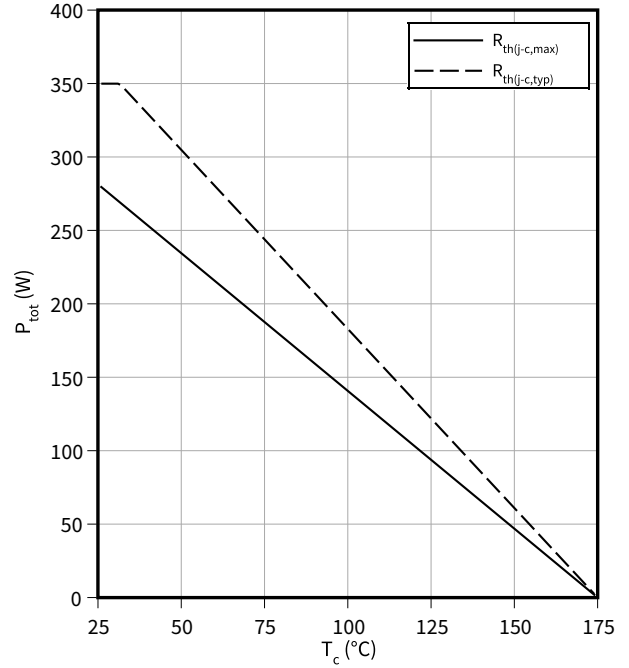
$$I_D = f(V_{DS})$$

$$T_{vj} \leq 175^\circ\text{C}, T_c = 25^\circ\text{C}$$



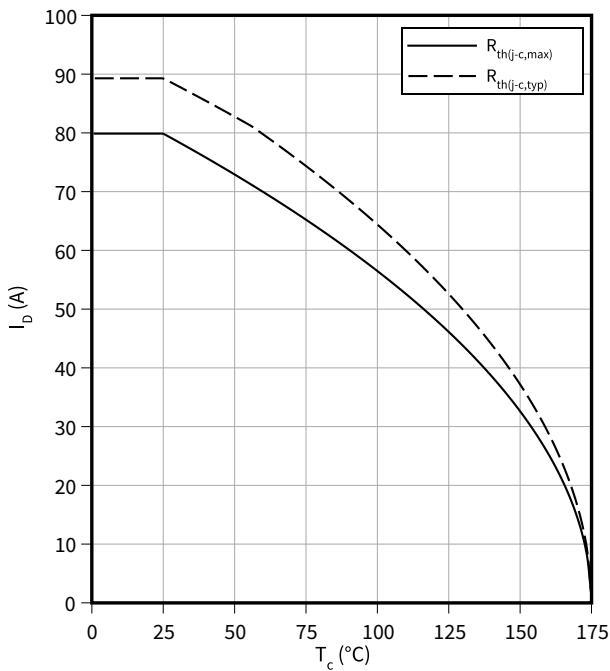
Power dissipation as a function of case temperature limited by bond wire

$$P_{tot} = f(T_c)$$



Maximum DC drain to source current as a function of case temperature limited by bond wire

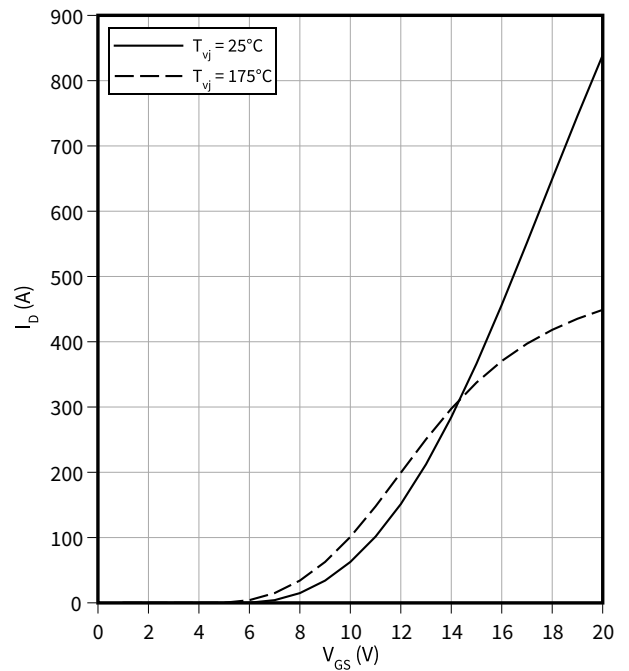
$$I_D = f(T_c)$$



Typical transfer characteristic

$$I_D = f(V_{GS})$$

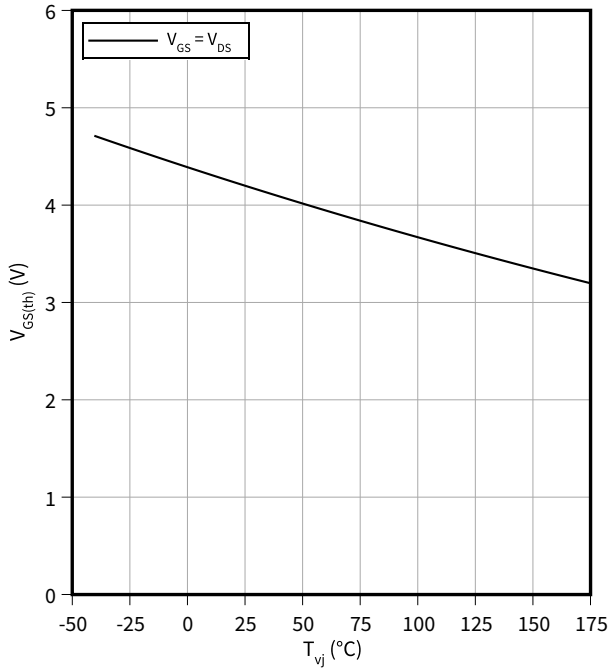
$$t_p = 20 \mu\text{s}, V_{DS} = 20 \text{ V}$$



4 Characteristics diagrams

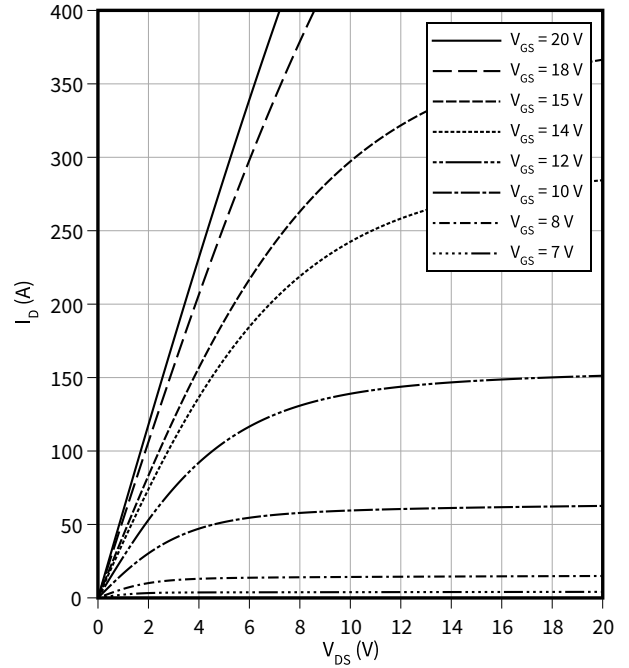
Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$
 $I_D = 11.8 \text{ mA}$



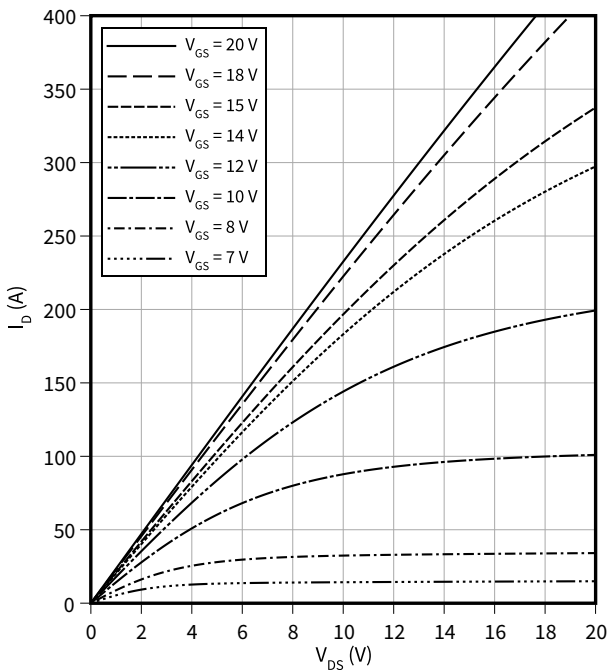
Typical output characteristic, V_{GS} as a parameter

$I_D = f(V_{DS})$
 $T_{vj} = 25 \text{ °C}, t_p = 20 \text{ } \mu\text{s}$



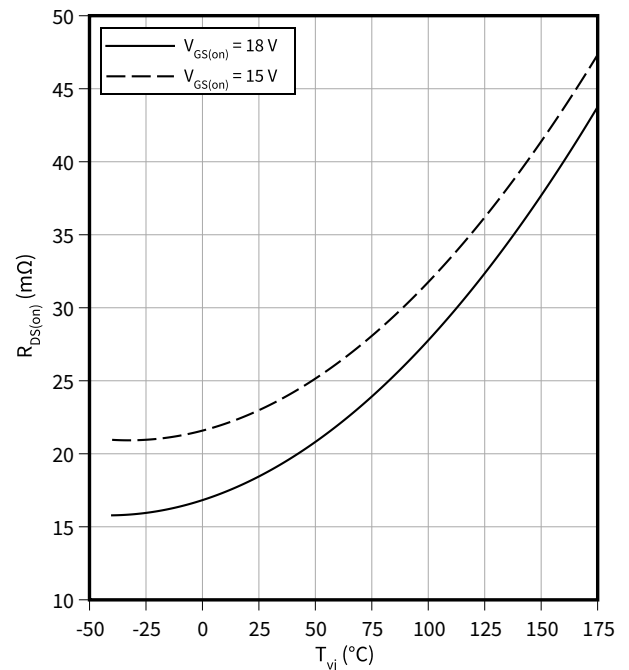
Typical output characteristic, V_{GS} as a parameter

$I_D = f(V_{DS})$
 $T_{vj} = 175 \text{ °C}, t_p = 20 \text{ } \mu\text{s}$



Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$
 $I_D = 37.4 \text{ A}$

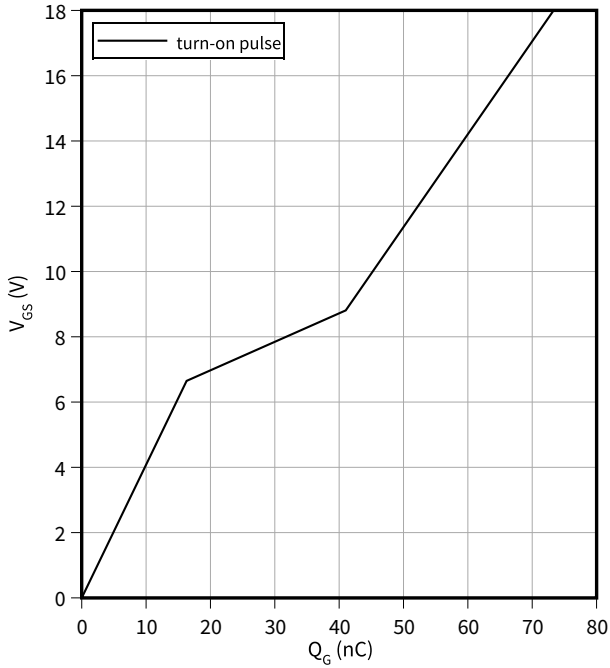


4 Characteristics diagrams

Typical gate charge

$V_{GS} = f(Q_G)$

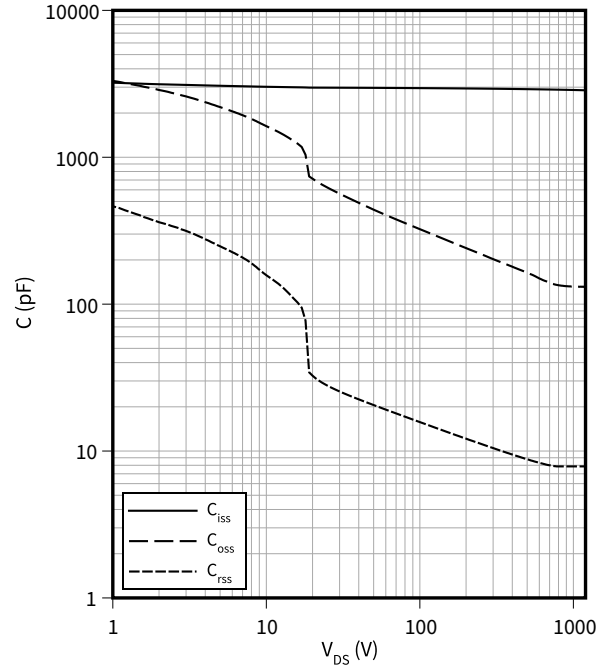
$I_D = 37.4 \text{ A}$, $V_{DS} = 800 \text{ V}$



Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$

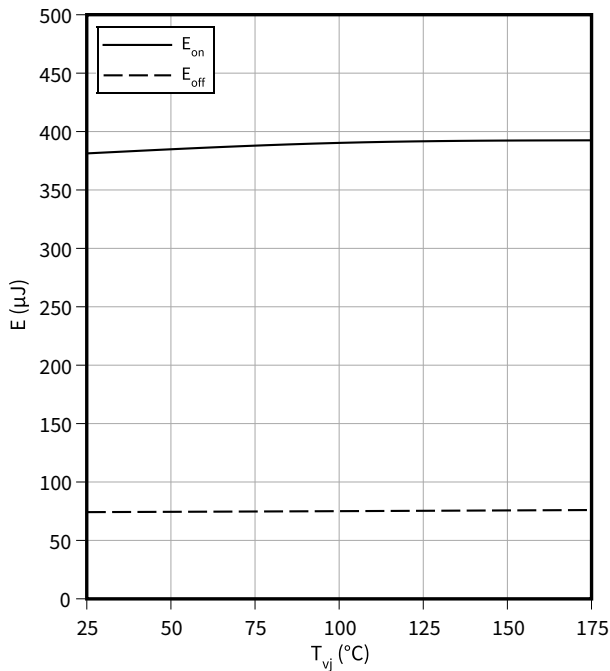
$f = 100 \text{ kHz}$, $V_{GS} = 0 \text{ V}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device external SiC diode

$E = f(T_{vj})$

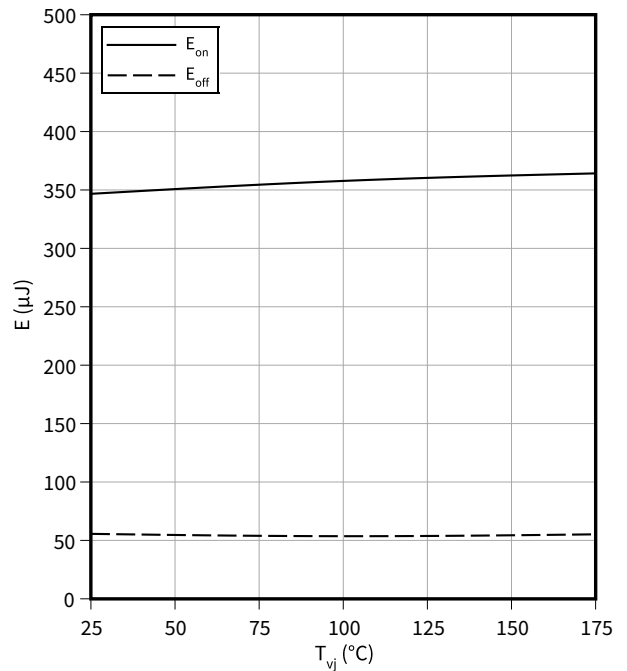
$V_{GS} = 0/18 \text{ V}$, $I_D = 37.4 \text{ A}$, $R_{G,ext} = 2.8 \Omega$, $V_{DD} = 800 \text{ V}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device external SiC diode

$E = f(T_{vj})$

$V_{GS} = -5/18 \text{ V}$, $I_D = 37.4 \text{ A}$, $R_{G,ext} = 2.8 \Omega$, $V_{DD} = 800 \text{ V}$

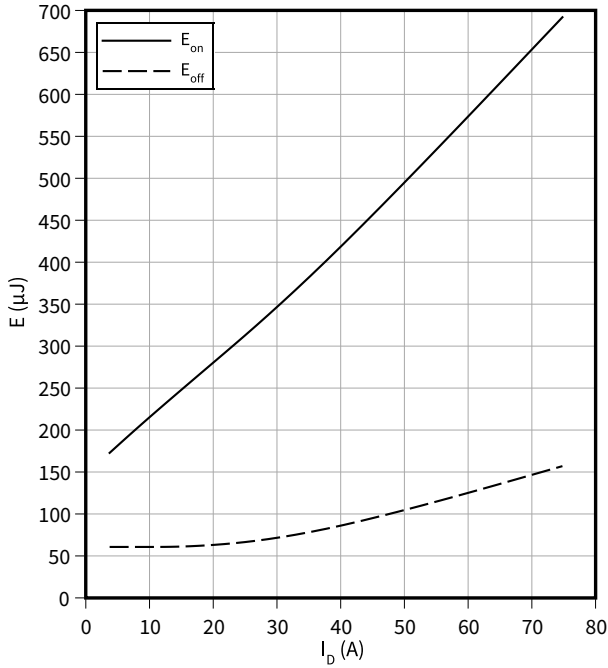


4 Characteristics diagrams

Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device external SiC diode

$E = f(I_D)$

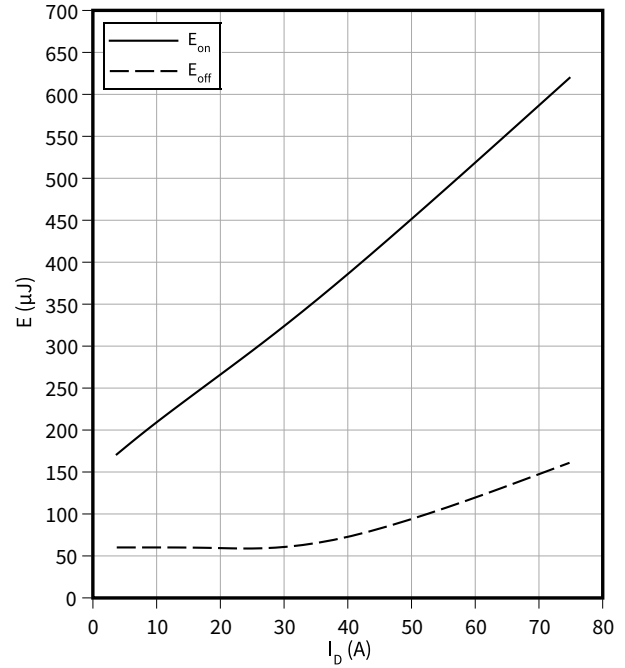
$V_{GS} = 0/18\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.8\ \Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device external SiC diode

$E = f(I_D)$

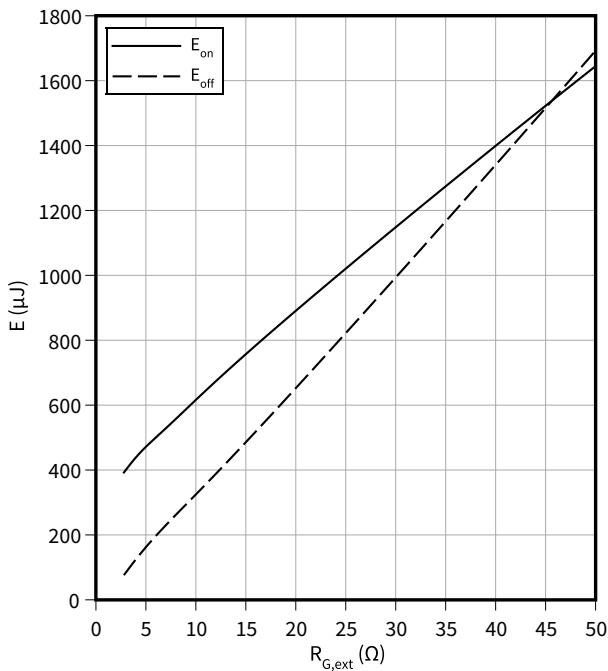
$V_{GS} = -5/18\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.8\ \Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device external SiC diode

$E = f(R_{G,ext})$

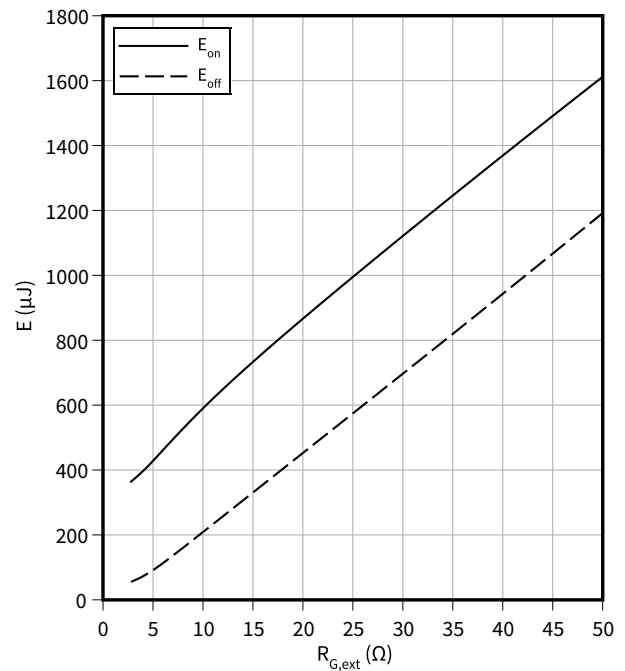
$V_{GS} = 0/18\text{ V}$, $I_D = 37.4\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device external SiC diode

$E = f(R_{G,ext})$

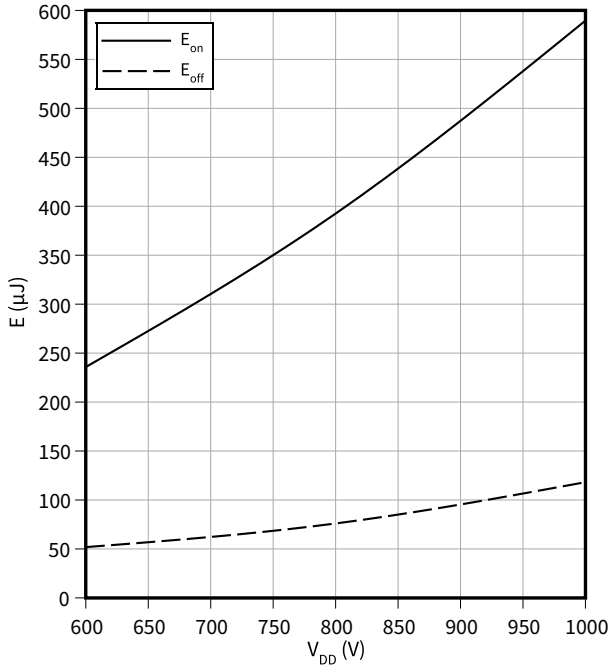
$V_{GS} = -5/18\text{ V}$, $I_D = 37.4\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$



4 Characteristics diagrams

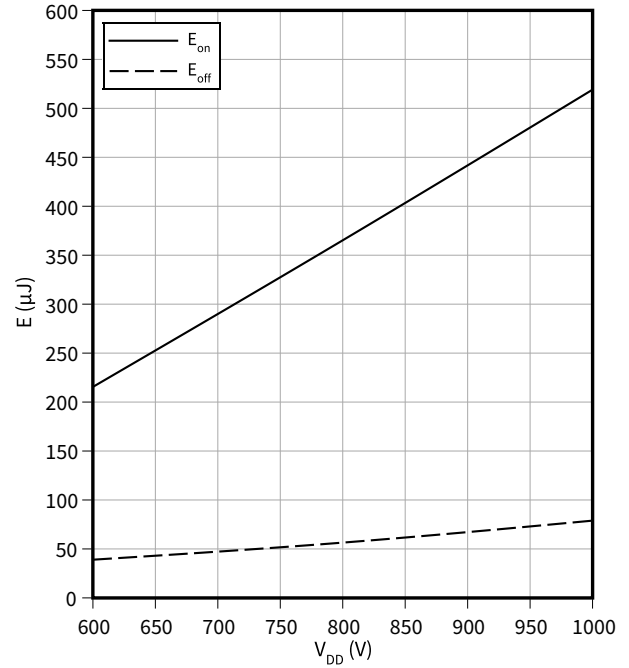
Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device external SiC diode

$E = f(V_{DD})$
 $V_{GS} = 0/18\text{ V}$, $I_D = 37.4\text{ A}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.8\text{ }\Omega$



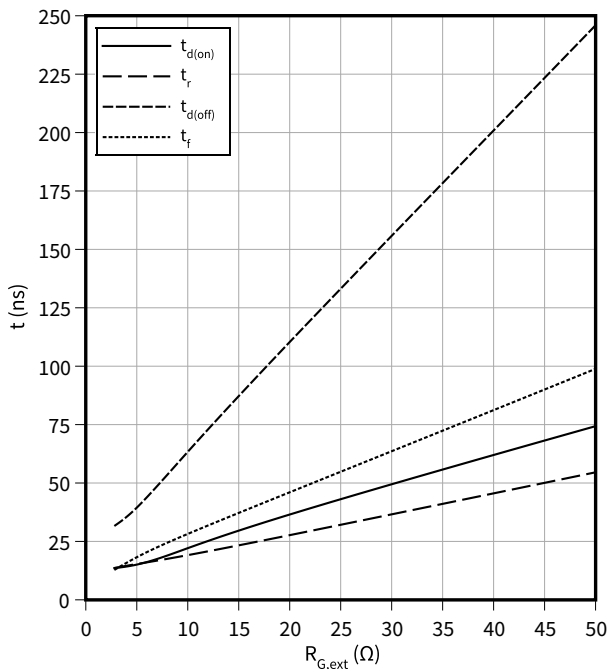
Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device external SiC diode

$E = f(V_{DD})$
 $V_{GS} = -5/18\text{ V}$, $I_D = 37.4\text{ A}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.8\text{ }\Omega$



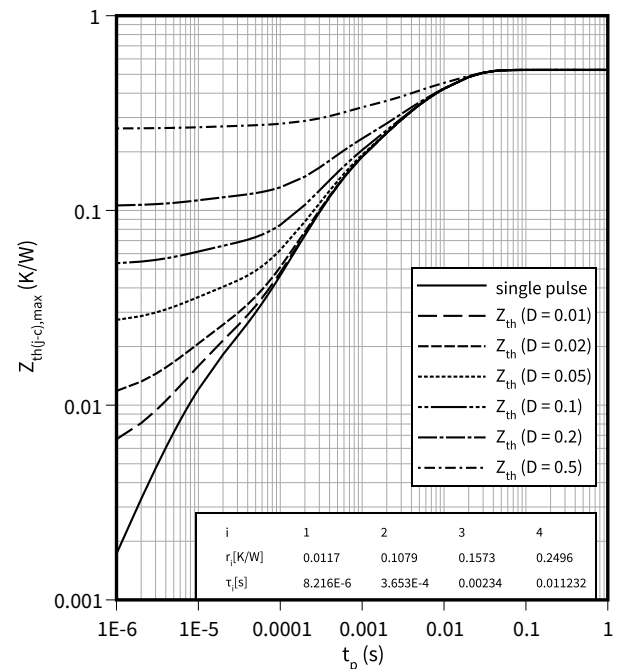
Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device external SiC diode

$t = f(R_{G,ext})$
 $V_{GS} = 0/18\text{ V}$, $I_D = 37.4\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$



Max. transient thermal impedance (MOSFET)

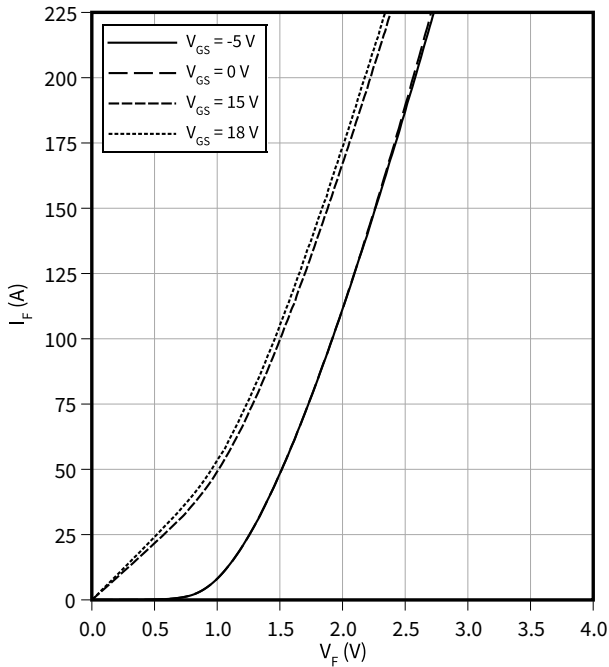
$Z_{th(j-c),max} = f(t_p)$
 $D = t_p/T$



4 Characteristics diagrams

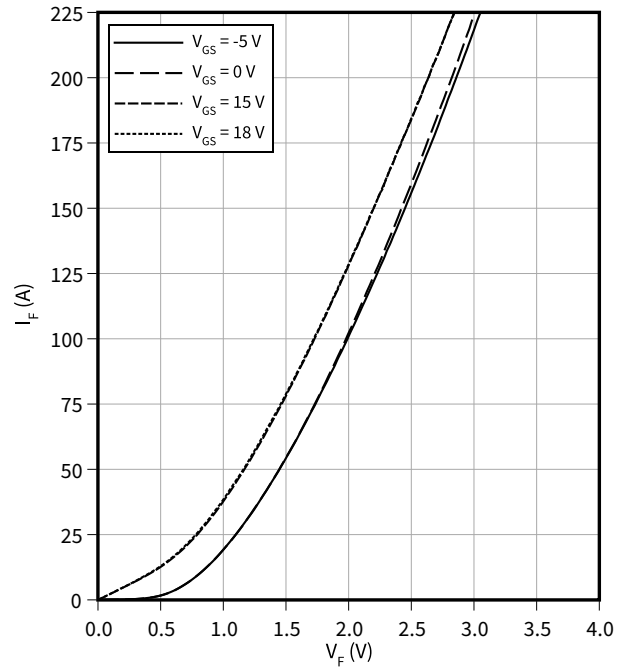
Typical diode forward current as a function of forward voltage, V_{GS} as a parameter

$I_F = f(V_F)$
 $t_p = 20 \mu s, T_{vj} = 25 \text{ }^\circ\text{C}$



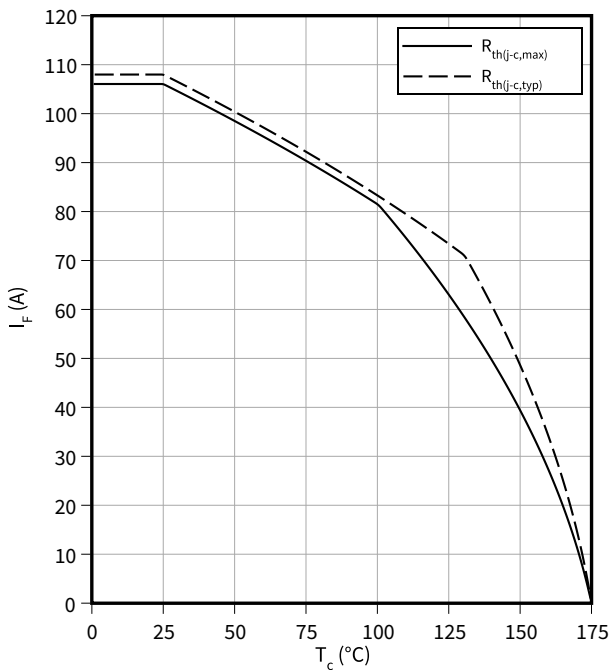
Typical diode forward current as a function of forward voltage, V_{GS} as a parameter

$I_F = f(V_F)$
 $t_p = 20 \mu s, T_{vj} = 175 \text{ }^\circ\text{C}$



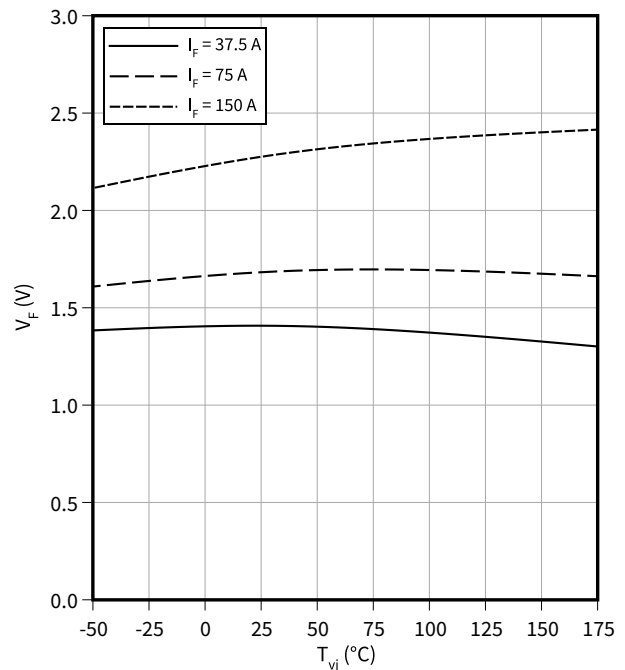
Maximum diode forward current as a function of case temperature limited by bond wire

$I_F = f(T_c)$
 $V_{GS} = 0 \text{ V}$



Typical diode forward voltage as function of junction temperature

$V_F = f(T_{vj})$
 $V_{GS} = 0 \text{ V}$

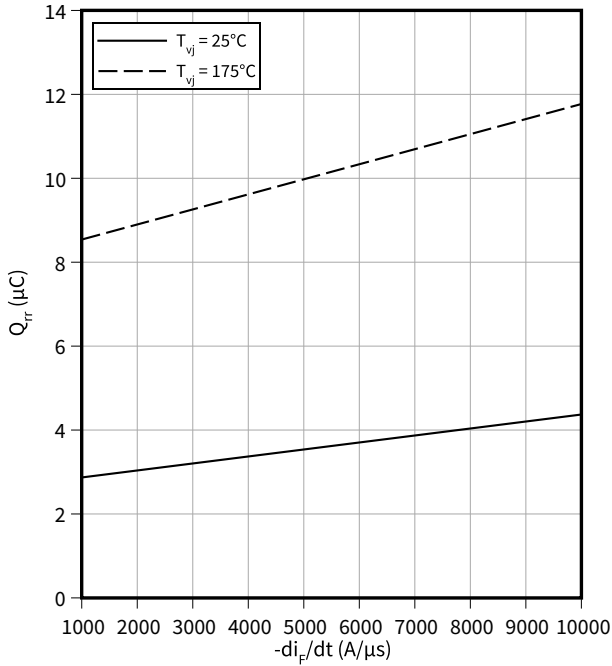


4 Characteristics diagrams

Typical reverse recovery charge as function of diode current slope, test circuit in Fig. G, 2nd device reverse-polarity protection co-packed diode

$$Q_{rr} = f(-di_F/dt)$$

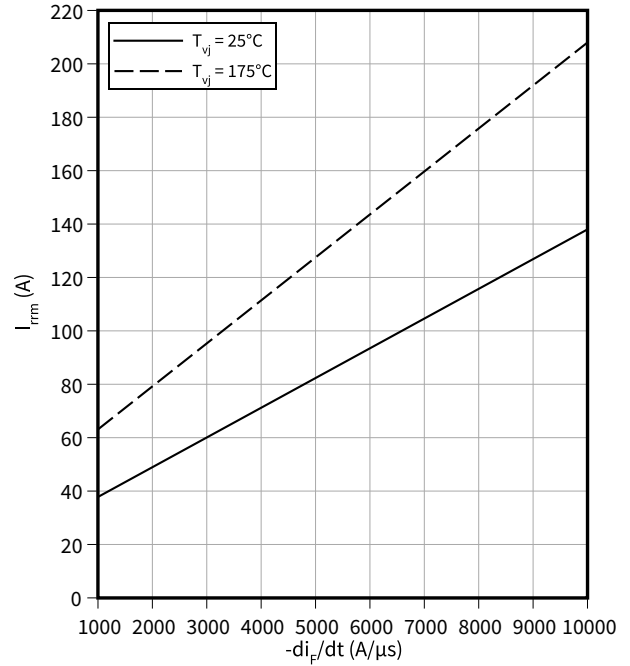
$V_{GS} = 0/18\text{ V}$, $V_{DD} = 800\text{ V}$, $I_F = 37.4\text{ A}$



Typical reverse recovery current as function of diode current slope, test circuit in Fig. G, 2nd device reverse-polarity protection co-packed diode

$$I_{rrm} = f(-di_F/dt)$$

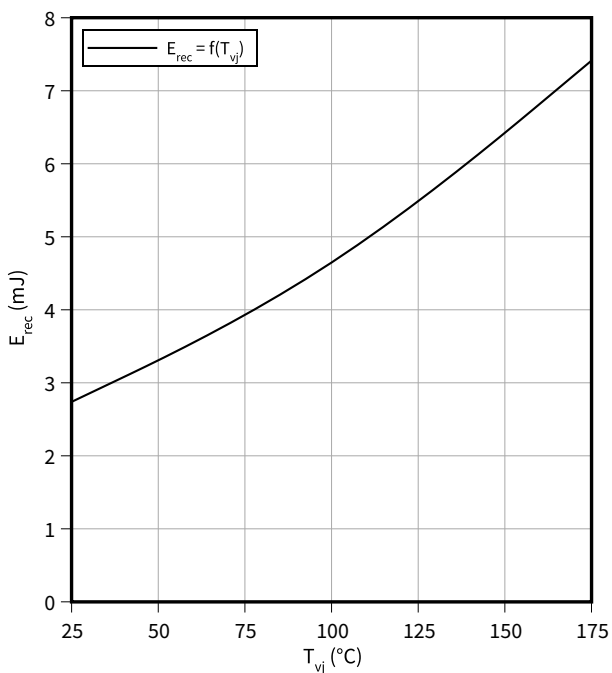
$V_{GS} = 0/18\text{ V}$, $V_{DD} = 800\text{ V}$, $I_F = 37.4\text{ A}$



Typical reverse energy losses as function of junction temperature, test circuit in Fig. G, 2nd device reverse-polarity protection co-packed diode

$$E_{rec} = f(T_{vj})$$

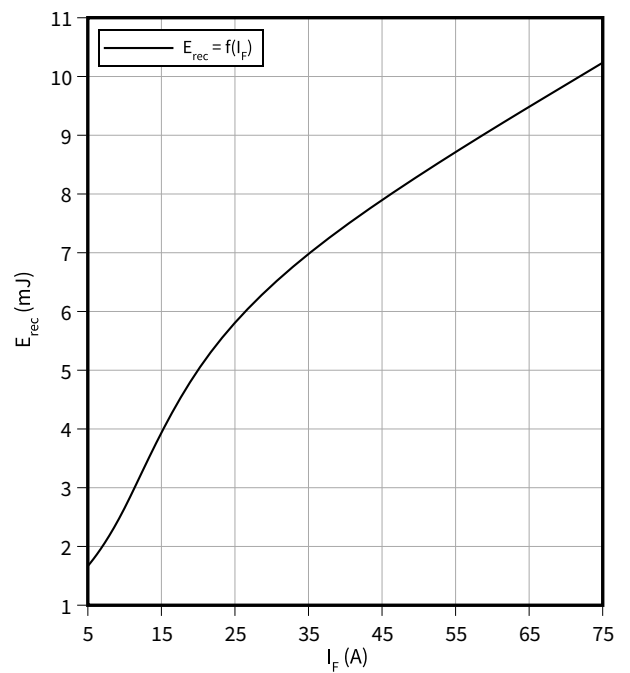
$V_{GS} = 0/18\text{ V}$, $R_{G,ext} = 2.8\ \Omega$, $V_{DD} = 800\text{ V}$, $I_F = 37.4\text{ A}$



Typical reverse energy losses as function of diode current, test circuit in Fig. G, 2nd device reverse-polarity protection co-packed diode

$$E_{rec} = f(I_F)$$

$V_{GS} = 0/18\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.8\ \Omega$, $V_{DD} = 800\text{ V}$

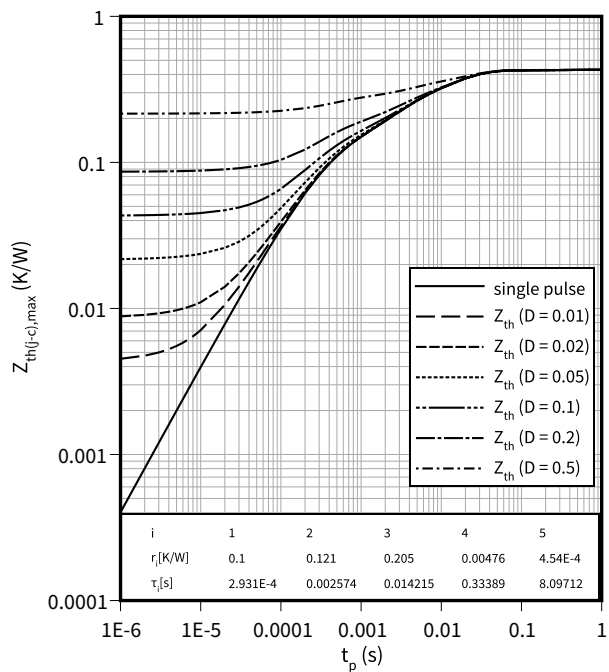


4 Characteristics diagrams

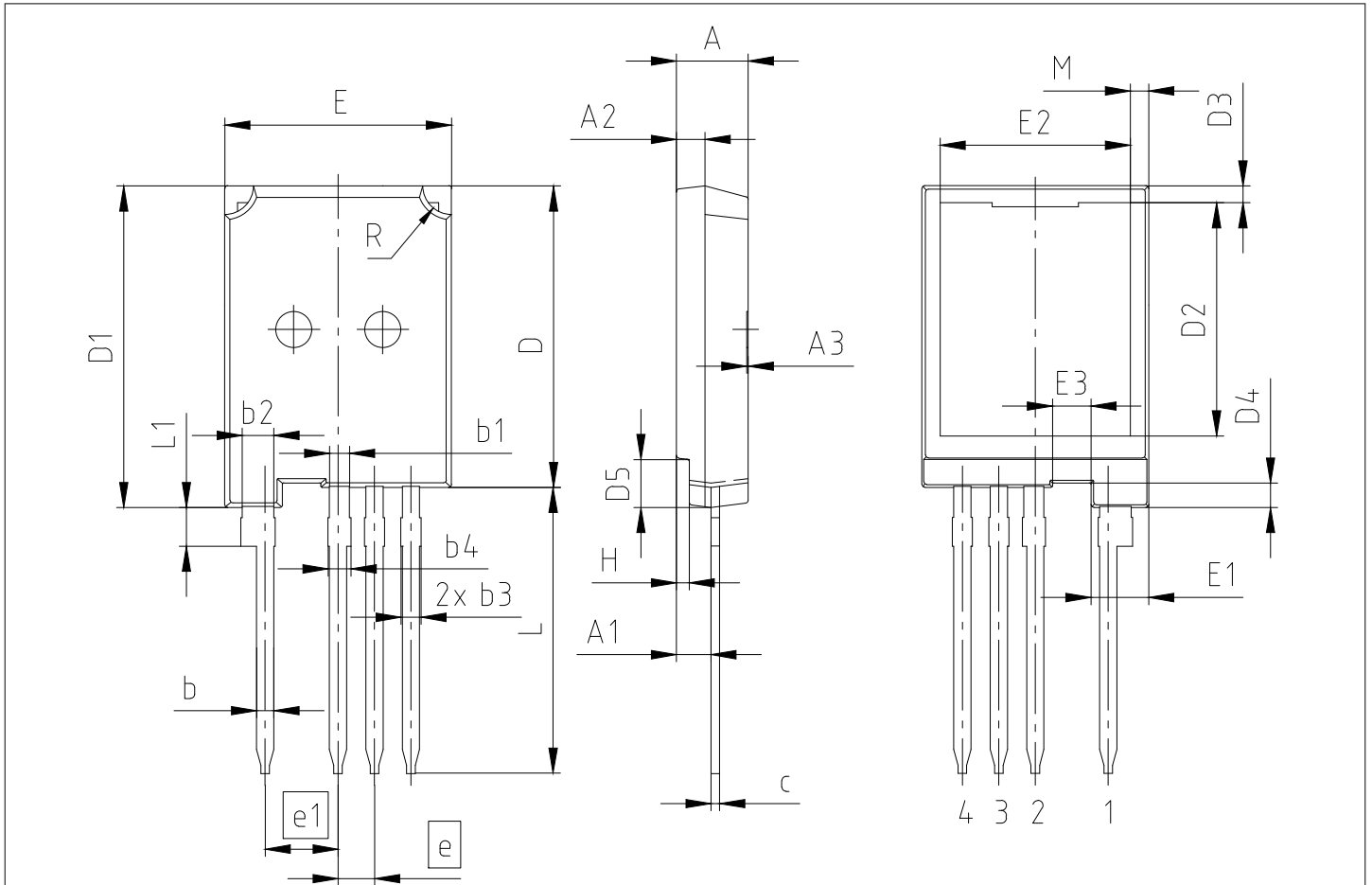
Max. transient thermal impedance (protection diode)

$$Z_{th(j-c),max} = f(t_p)$$

$$D = t_p/T$$



5 Package outlines



NOTES:
PACKAGE SURFACE ROUTE BETWEEN PIN 1 & PIN 2 WILL BE 5.1 mm MIN.
ALL b... AND c DIMENSIONS INCLUDING PLATING EXPECT AREA OF CUTTING

PACKAGE - GROUP NUMBER:		PG-TO247-4-U10			
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.70	15.90
A1	2.31	2.51	E1	3.90	4.10
A2	1.90	2.10	E2	13.10	13.50
b	1.16	1.29	E3	2.58	2.78
b1	1.36	1.49	e	2.54	
b2	2.16	2.29	e1	5.08	
b3	1.16	1.45	H	0.80	1.00
b4	1.16	1.65	N	4	
c	0.59	0.66	L	19.80	20.10
D	20.90	21.10	L1	2.55	2.85
D1	22.30	22.50	M	0.97	1.57
D2	15.95	16.55	R	1.90	2.10
D3	1.00	1.35			
D4	1.60	1.80			
D5	3.24	3.44			

Figure 1

6 Testing conditions

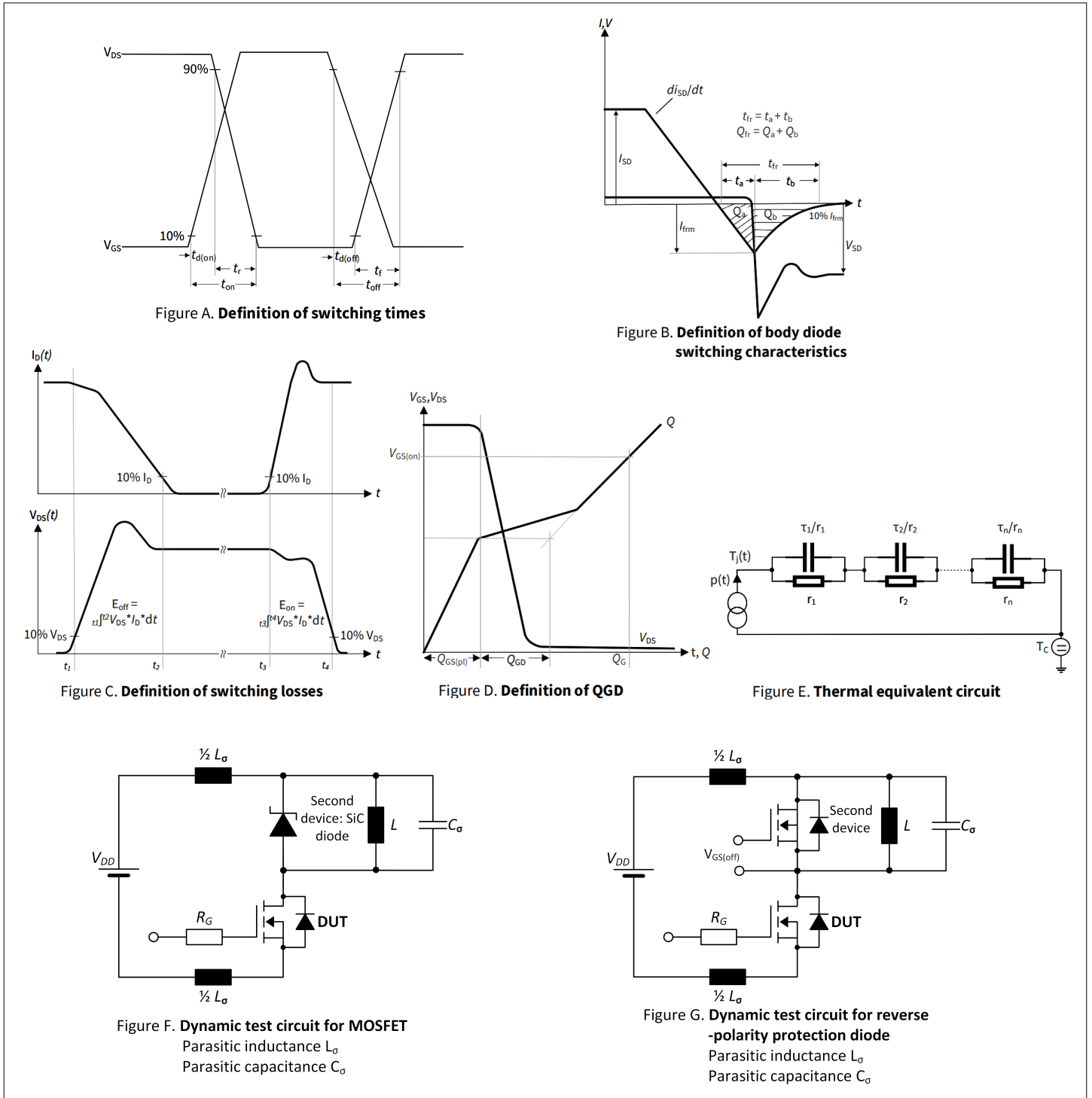


Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2025-03-12	Target datasheet
0.20	2025-08-08	Preliminary datasheet
1.00	2025-11-20	Final datasheet

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